

Thursday 31 May

09:00

Detector Characterization and Simulations

Session | Location: Bari | Conveners: Eckhart Fretwurst, Vladimir Eremin

09:00-09:20

FORMATION AND ANNEALING OF INTERSTITIAL DEFECTS IN P-TYPE SILICON AND SILICON-GERMANIUM ALLOYS UNDER ELECTRON AND ALPHA-IRRADIATION

Speaker

Dr Leonid Makarenko

09:20-09:40

Irradiation study on diodes of different silicon materials for the CMS tracker upgrade

Speaker

Joachim Erfle

09:40-10:00

Impact of proton irradiations with different particle-energies on the electrical properties of Si-diodes

Speaker

Coralie Neubuser

10:00-10:20

Operational conditions for enhancement of collected charge via avalanche multiplication in n-on-p strip detectors

Dr Elena Verbitskava

10:20-10:50 Coffee Break

10:50-11:10

Analysis of Edge and Surface TCTs for Irradiated 3D Silicon Strip Detectors

Speaker

Graeme Douglas Stewart

11:10-11:30

Characterization of Micron n-on-p ministrip sensors irradiated with 24 GeV/c protons.

Speaker

Nicola Pacifico

11:30-11:50

Charge collection studies on heavily irradiated diodes from the RD50 multiplication run

Speaker

Gregor Kramberger

11:50-12:10 Thin Irradiated Strip and Pixel Detectors

Speaker

Philipp Weigell

12:10-12:30 Low cost commercial scanning TCT setup

Speaker

Gregor Kramberger

12:30-13:00

TCAD Simulation of irradiated Silicon radiation detector using commercial simulation products

Speaker

Mathieu Benoit

13:00-14:00 Lunch

14:00-14:20

Electric Field Modeling by simulations with ISE-TCAD

Speaker

Mercedes Minano Moya

14:20-14:40 Simulation of the Double Peak Effect in irradiated Sensors

Speaker

Robert Eber

14:40-15:00

Isolation Characteristics of Silicon Sensors Using Simulation Approach

Speaker

Dr Kirti Ranjan

15:00-15:30 Discussion - Simulation Working Group

Speakers

Eckhart Fretwurst, Vladimir Eremin

15:30